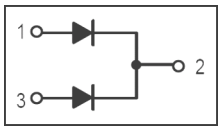
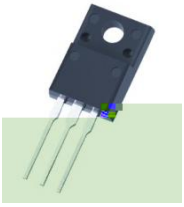
TO-220F

Ultrafast Recovery Diode in a TO-220F Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode



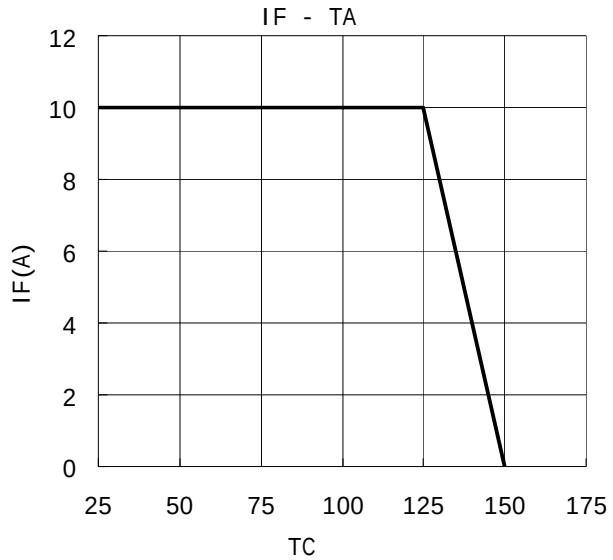


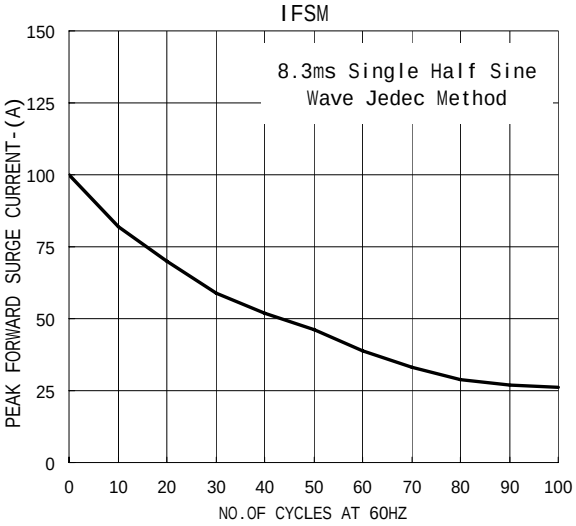
PIN1 Anode PIN2 Cathode PIN 3 Anode

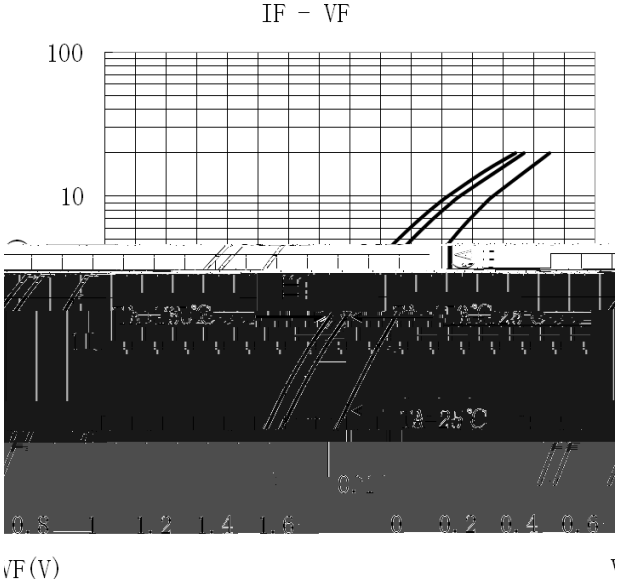
See Marking Instructions

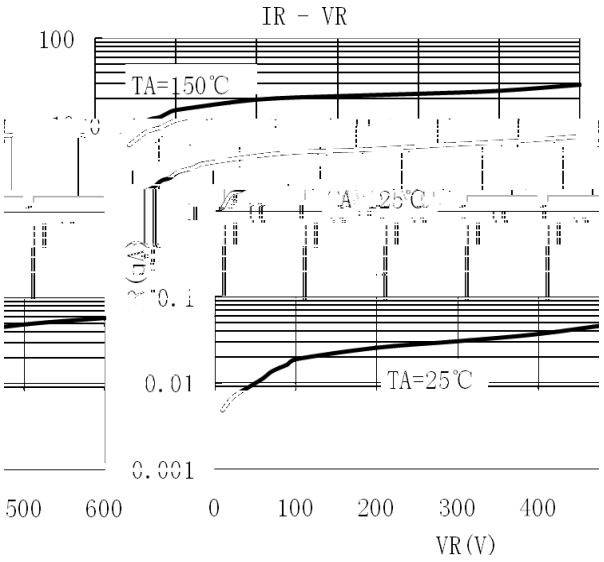
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Reverse Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Forward Current	I_F	2 × 5	A
Peak forward surge current	I_{FSM}	100	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	4	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

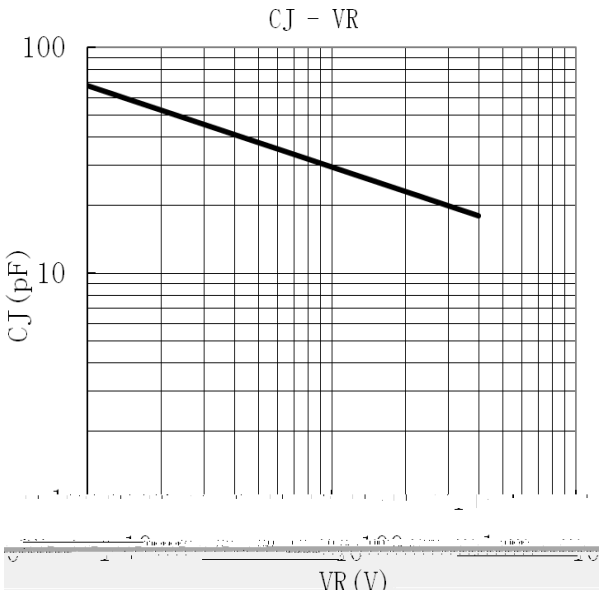
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	I_R=1mA	600			V
Forward Voltage	V_F	I_F=1A T_C=25		0.91	1.05	V
		I_F=1A T_C=125		0.74	0.95	
		I_F=5A T_C=25		1.15	1.5	
		I_F=5A T_C=125		1.0	1.2	
Instantaneous Reverse Current	I_R					

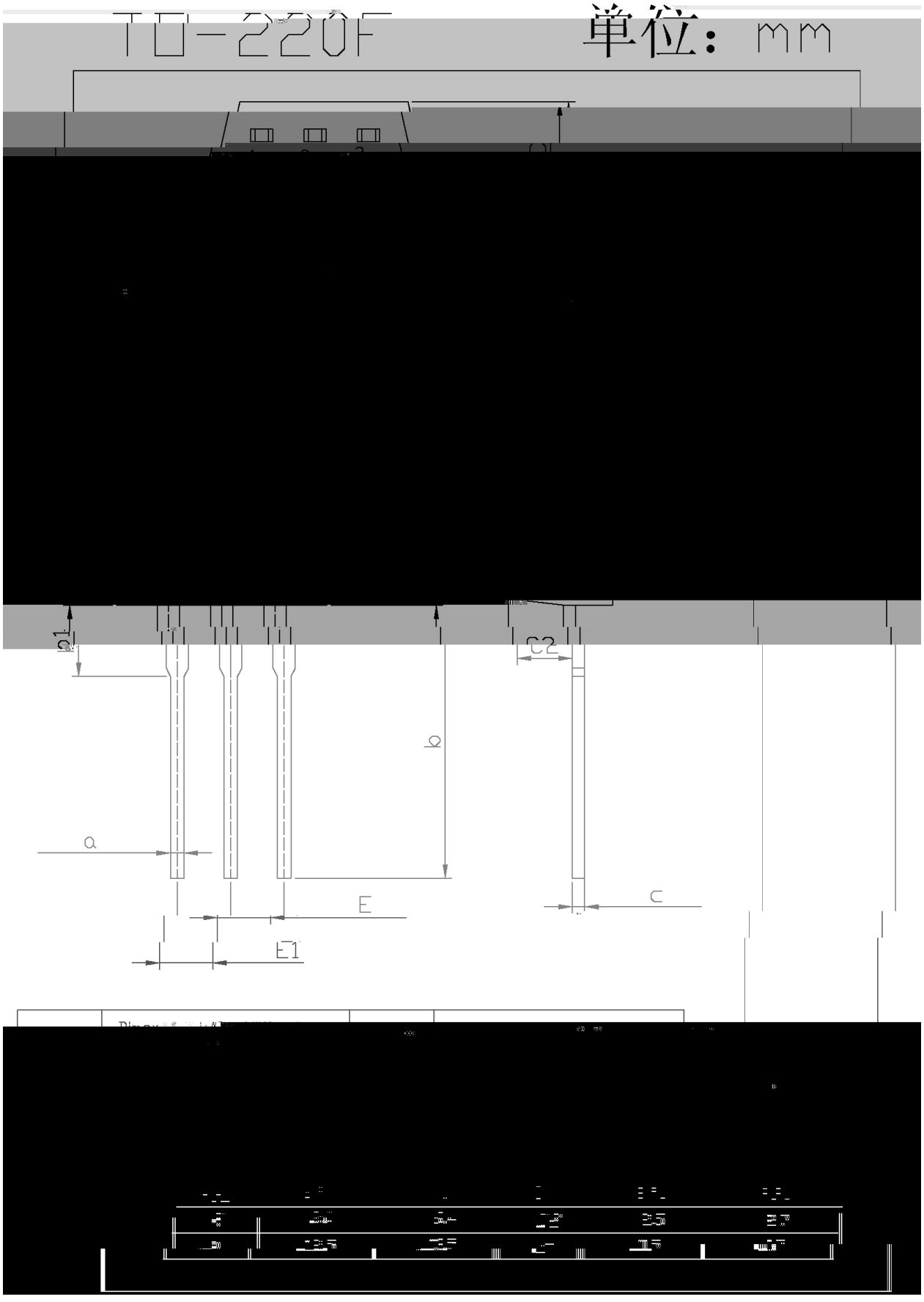

IF - TA
12
10
8
6
4
2
0
IF(A)
25
50
75
100
125
150
175
TC

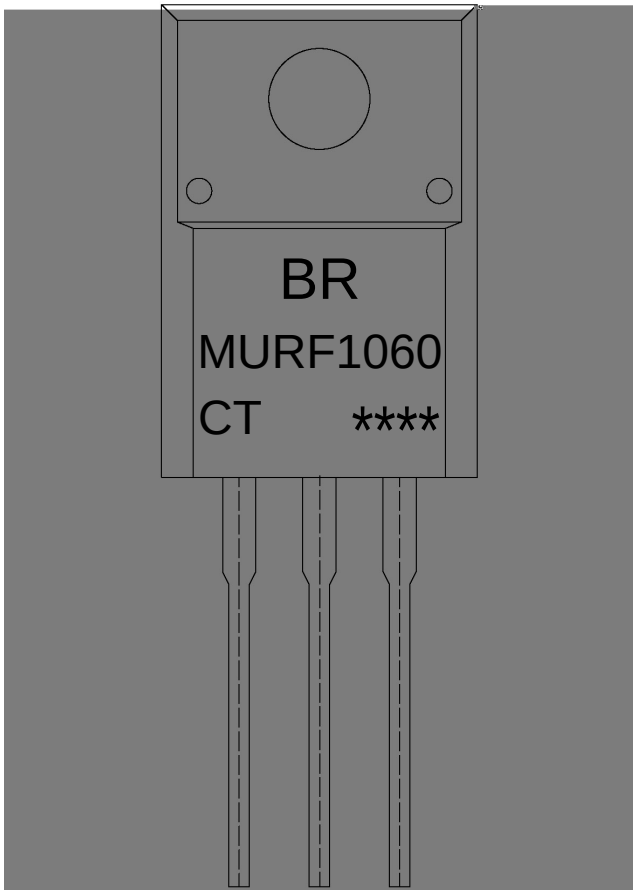

IFSM
8.3ms Single Half Sine
Wave Jedec Method
150
125
100
75
50
25
0
PEAK FORWARD SURGE CURRENT-(A)
0
10
20
30
40
50
60
70
80
90
100
NO.OF CYCLES AT 60HZ


IF - VF
100
10
VF(V)


IR - VR
100
TA=150℃
TA=25℃
0.01
0.001
500
600
0
100
200
300
400
VR(V)


CJ - VR
100
10
CJ(pF)
VR(V)


TO-220F
单位：mm
b2
c2
b
a
E
c
E1



BR

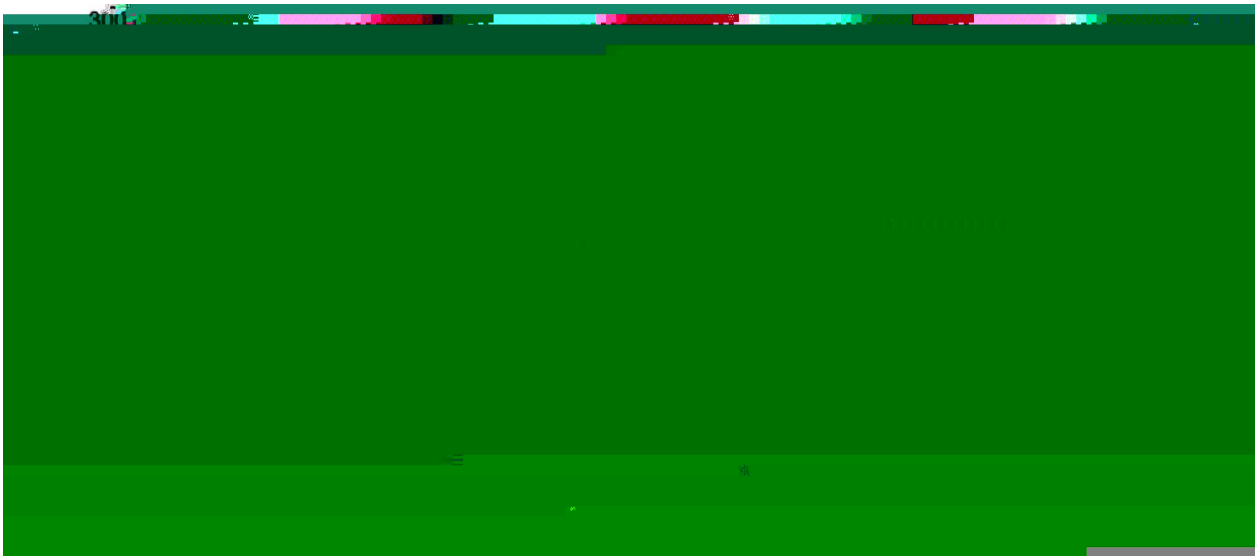
MURF1060

CT:

****

Note:

BR:	Company Code
MURF1060	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ BULK

Package Type	Units			Dimension (unit mm^3)
	Units/Bag	Bags/Inner Box	Units/Inner Box	
	/	/	/	